

Dual Series Switching Diode
Reverse Voltage 75 Volts Forward Current 0.215 Ampere

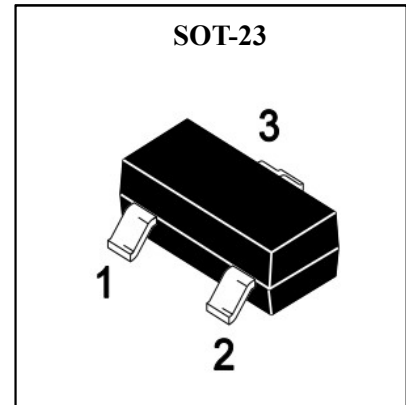
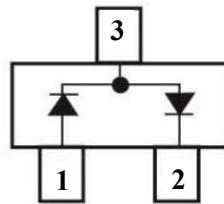
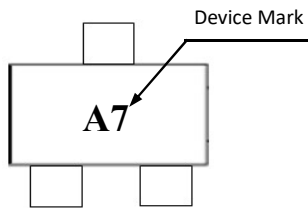
Features

- High switching speed
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

Typical Applications

- High-speed switching.

Marking



Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

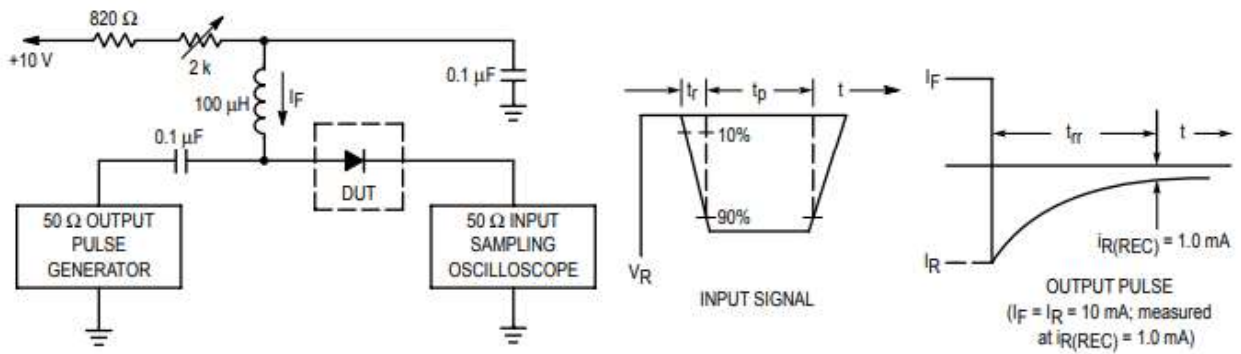
Parameter	Symbol	Rated Value	Unit
Continuous Reverse Voltage	V_R	75	V
Forward Current	I_F	215	mA
Peak Forward Surge Current	$I_{FM}(\text{surge})$	500	mA
Average Rectified Forward Current (averaged over any 20ms period)	$I_{F(AV)}$	715	mA
Total Device Dissipation, FR-5 Board ⁽¹⁾ Ta=25°C Derate above 25°C	PD	225	mW
		1.8	mW/°C
Non-Repetitive Peak Forward Current $t=1\mu\text{s}$ $t=1\text{ms}$ $t=1\text{s}$	IFSM	2	A
		1	
		0.5	
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	Rth(j-a)	556	°C/W
Junction and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

1. FR-5=1.0×0.75×0.062 in.

Electrical Characteristics (Ta=25°C unless otherwise noted)

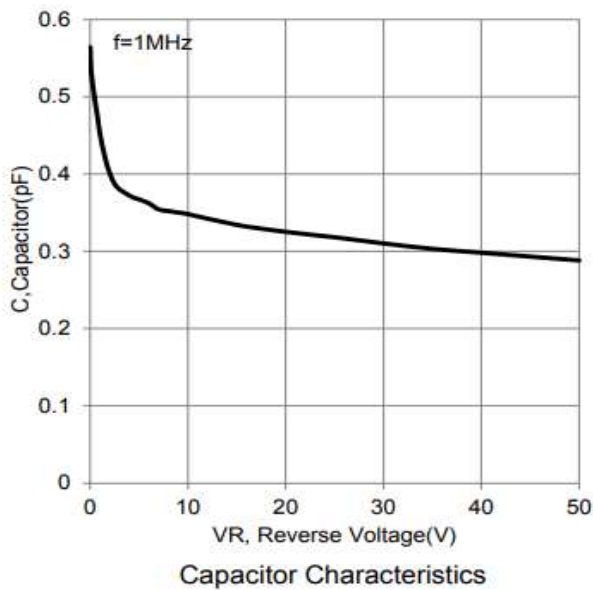
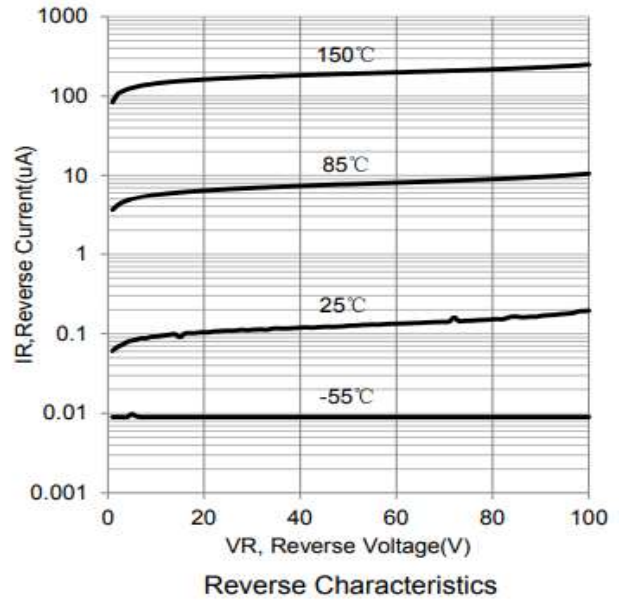
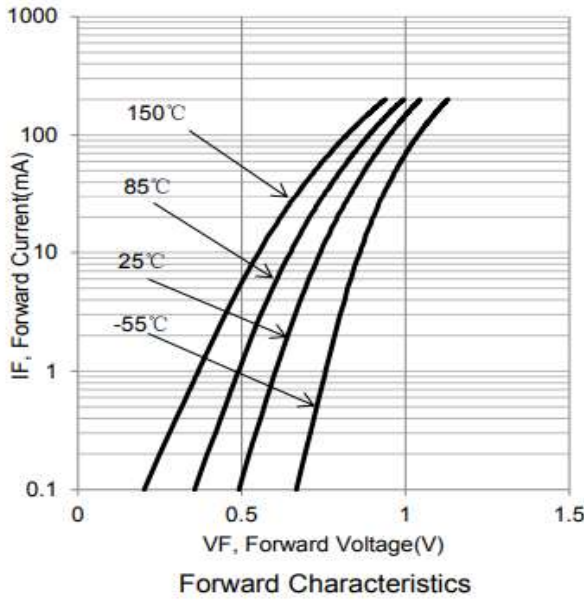
Parameter	Symbol	Conditions	Min	Max	Unit
Reverse Breakdown Voltage	V_{BR}	$I_R = 100\mu\text{A}$	75	-	V
Forward Voltage	V_F	$I_F = 1.0\text{mA}$	-	715	mV
		$I_F = 10\text{mA}$	-	855	
		$I_F = 50\text{mA}$	-	1000	
		$I_F = 150\text{mA}$	-	1250	
Reverse Voltage Leakage Current	I_R	$V_R = 75\text{V}$	-	2.5	uA
		$V_R = 75\text{Vdc}, T_J=150^\circ\text{C}$	-	50	
		$V_R = 25\text{Vdc}, T_J=150^\circ\text{C}$	-	30	
Capacitance Between Terminals	C_T	$V_R=0\text{V}, f=1\text{MHz}$	-	2.0	pF
Forward Recovery Voltage	V_{FR}	$I_F = 10\text{mA}, t_f=20\text{ns}$	-	1.75	Vdc
Reverse Recovery Time	t_{rr}	$I_F=I_R=10\text{mA}, I_{RR}=1\text{mA}, R_L=50\Omega$	-	6.0	ns

Electrical Characteristics Curves (Ta=25°C unless otherwise noted)

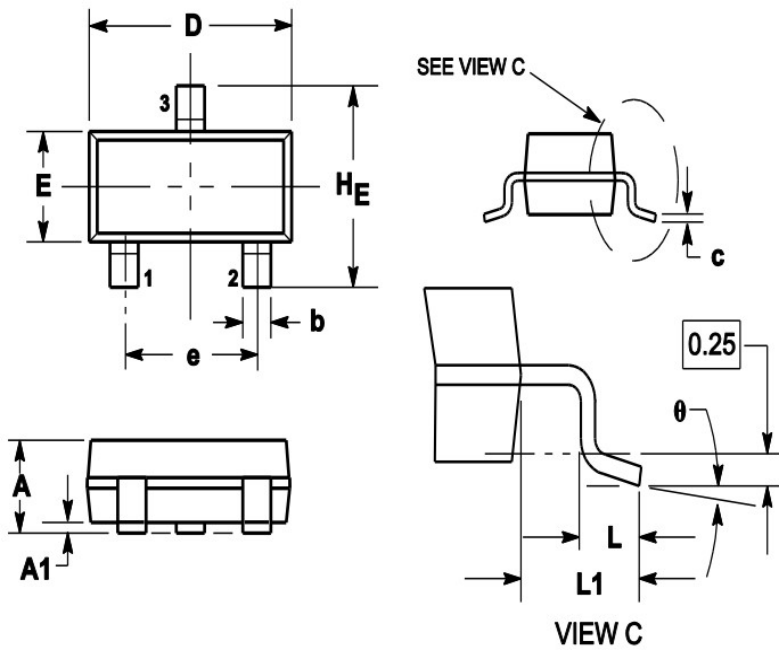


- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
- 2. Input pulse is adjusted so $I_R(\text{peak})$ is equal to 10 mA.
- 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit



Package Outline and Dimensions



Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

Soldering Footprint

